

Yeqing Lu

List of Publications by Year in descending order

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19
papers

1,072
citations

840776

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1125743

13
g-index

19
all docs

19
docs citations

19
times ranked

1246
citing authors

#	ARTICLE	IF	CITATIONS
1	Tunnel Field-Effect Transistors: State-of-the-Art. IEEE Journal of the Electron Devices Society, 2014, 2, 44-49.	2.1	511
2	AlGaSb/InAs Tunnel Field-Effect Transistor With On-Current of 78 $\mu\text{A}/\mu\text{m}$ at 0.5 V. IEEE Electron Device Letters, 2012, 33, 363-365.	3.9	129
3	Performance of AlGaSb/InAs TFETs With Gate Electric Field and Tunneling Direction Aligned. IEEE Electron Device Letters, 2012, 33, 655-657.	3.9	103
4	Universal analytic model for tunnel FET circuit simulation. Solid-State Electronics, 2015, 108, 110-117.	1.4	81
5	Monolayer Solid-State Electrolyte for Electric Double Layer Gating of Graphene Field-Effect Transistors. ACS Nano, 2017, 11, 5453-5464.	14.6	40
6	InAs/AlGaSb heterojunction tunnel field-effect transistor with tunnelling in-line with the gate field. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 389-392.	0.8	39
7	Continuous semiempirical model for the current-voltage characteristics of tunnel fets. , 2014, , .		24
8	Electric Double Layer Dynamics in Poly(ethylene oxide) LiClO ₄ on Graphene Transistors. Journal of Physical Chemistry C, 2017, 121, 16996-17004.	3.1	24
9	Steep subthreshold swing tunnel FETs: GaN/InN/GaN and transition metal dichalcogenide channels. , 2015, , .		18
10	Scalability of Atomic-Thin-Body (ATB) Transistors Based on Graphene Nanoribbons. IEEE Electron Device Letters, 2010, 31, 531-533.	3.9	17
11	Perspectives of TFETs for low power analog ICs. , 2012, , .		17
12	Universal charge-conserving TFET SPICE model incorporating gate current and noise. IEEE Journal on Exploratory Solid-State Computational Devices and Circuits, 2016, , 1-1.	1.5	16
13	Steep slope transistors: Tunnel FETs and beyond. , 2016, , .		16
14	Tunnel FET Analog Benchmarking and Circuit Design. IEEE Journal on Exploratory Solid-State Computational Devices and Circuits, 2018, 4, 19-25.	1.5	13
15	Quantum Transport in AlGaSb/InAs TFETs With Gate Field In-Line With Tunneling Direction. IEEE Transactions on Electron Devices, 2015, 62, 2445-2449.	3.0	11
16	Solution-Cast Monolayers of Cobalt Crown Ether Phthalocyanine on Highly Ordered Pyrolytic Graphite. Journal of Physical Chemistry C, 2015, 119, 21992-22000.	3.1	9
17	An accurate interband tunneling model for InAs/GaSb heterostructure devices. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 740-743.	0.8	3
18	Tunnel field-effect transistors - update. , 2014, , .		1

#	ARTICLE	IF	CITATIONS
19	Fabrication approach for lateral InGaAs tunnel transistors. , 2009, , .		0